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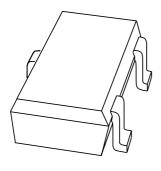
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



BFS20WNPN medium frequency transistor

Product data sheet 1999 Apr 21



NPN medium frequency transistor

BFS20W

FEATURES

- Low current (max. 25 mA)
- Low voltage (max. 20 V).
- Very low feedback capacitance (typ. 350 fF).

APPLICATIONS

• IF and VHF applications in thick and thin-film circuits.

DESCRIPTION

NPN medium frequency transistor in a SOT323 (SC-70) plastic package.

MARKING

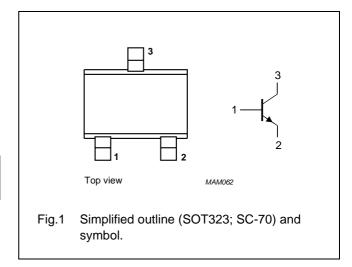
TYPE NUMBER	MARKING CODE ⁽¹⁾
BFS20W	N1*

Note

- 1. * = -: Made in Hong Kong.
 - * = t: Made in Malaysia.

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	30	V
V _{CEO}	collector-emitter voltage	open base	_	20	V
V _{EBO}	emitter-base voltage	open collector	_	4	V
I _C	collector current (DC)		_	25	mA
I _{CM}	peak collector current		_	25	mA
I _{BM}	peak base current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Refer to SOT323 (SC-70) standard mounting conditions.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Refer to SOT323 (SC-70) standard mounting conditions.

CHARACTERISTICS

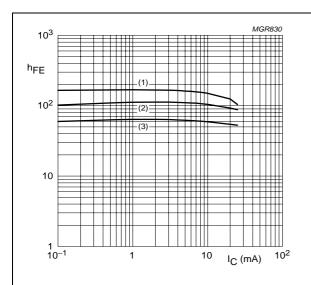
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 20 V	_	_	100	nA
		I _E = 0; V _{CB} = 20 V; T _j = 100 °C	_	_	10	μΑ
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 4 V	_	_	100	nA
h _{FE}	DC current gain	I _C = 7 mA; V _{CE} = 10 V	40	85	_	
V_{BE}	base-emitter voltage	$I_C = 7 \text{ mA}; V_{CE} = 10 \text{ V}$	_	740	900	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 10 \text{ V}$; $f = 1 \text{ MHz}$	_	1	_	pF
C _{re}	feedback capacitance	I _C = 0; V _{CE} = 10 V; f = 1 MHz	_	350	_	fF
f _T	transition frequency	I _C = 5 mA; V _{CE} = 10 V; f = 100 MHz	360	470	_	MHz

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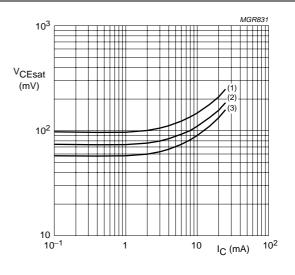
BFS20W



 $V_{CE} = 10 \text{ V}.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

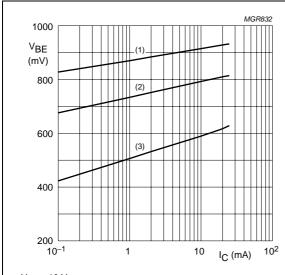
Fig.2 DC current gain as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 10.$

- (1) $T_{amb} = 100 \, ^{\circ}C$.
- (2) T_{amb} = 25 °C.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

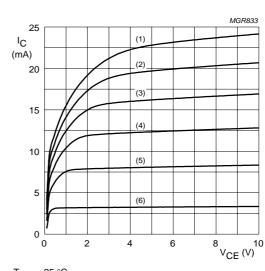
Fig.3 Collector-emitter saturation voltage as a function of collector current; typical values.



 $V_{CE} = 10 \text{ V}.$

- (1) $T_{amb} = -100 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.4 Base-emitter voltage as a function of collector current; typical values.



 $T_{amb} = 25 \, ^{\circ}C$.

- (1) $I_B = 280 \mu A$.
- (4) $I_B = 130 \mu A$.
- (2) $I_B = 230 \mu A$.
- (5) $I_B = 80 \mu A$.
- (3) $I_B = 180 \,\mu\text{A}$.
- (6) $I_B = 30 \mu A$.

Fig.5 Collector current as a function of collector-emitter voltage; typical values.

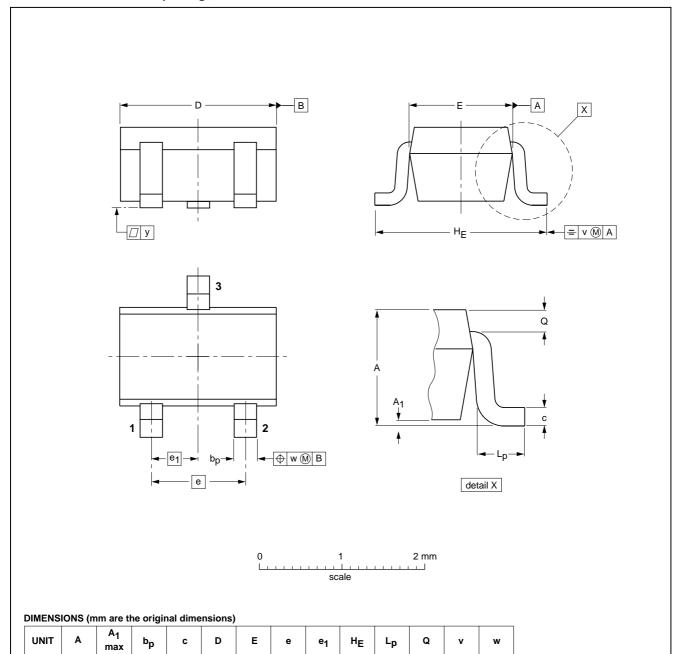
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



OUTLINE		REFERENCES		EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT323			SC-70			97-02-28

0.45 0.15

0.23

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0.4

0.3

0.25 0.10 2.2 1.8 1.35 1.15

1.1 0.8

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Customer notification

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Contact information

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